

Please amend the following claims to the state indicated below.

1. (Once amended) A process of PECVD deposition of metal films comprising the steps of:
providing an ion promoting atmosphere; and

A2 *5/13* contacting a substrate with a plasma of approximately 50 to 90 % of a metal-containing gas in said ion promoting atmosphere at a pressure and temperature range sufficient for film deposition for said metal.

29. (Once amended) A process for PECVD deposition of metal-containing films on a surface, the process comprising:

A3 maintaining a pressure and a temperature which allow for PECVD metal-containing film deposition; and

contacting said surface with a plasma of approximately 50 to 90% metal-containing compound in a chemically inert atmosphere.

A marked-up version of these amended claims appears in an appendix to this Preliminary Amendment.

REMARKS

Claims 1-66 are part of the original specification.

Claims 5-28 and 30-66 are cancelled without prejudice.

Claims 1 and 29 are amended.

Claims 1-4, and 29 are pending.

Applicants note that the specification of this continuation has been altered from that of the parent by providing paragraph numbering and by fixing a typographical error in the title as it appears on page 1, after the cover page.

In the interest of efficient prosecution, Applicants also note that claims 1-4 and 29 were prosecuted in the parent application and rejected in an Office Action dated February 9, 2001